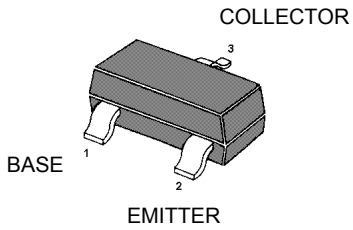
TRANSISTOR (NPN)



FEATURES

Complimentary to SS8550

MARKING: Y1

SOT-23

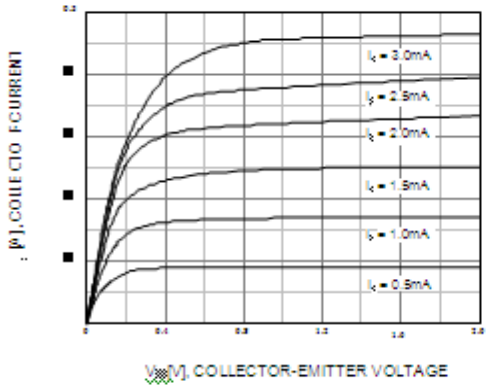
MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

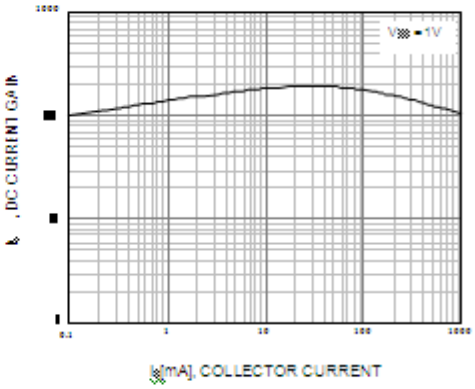
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1.5	A
P_C	Collector Power Dissipation	0.3	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

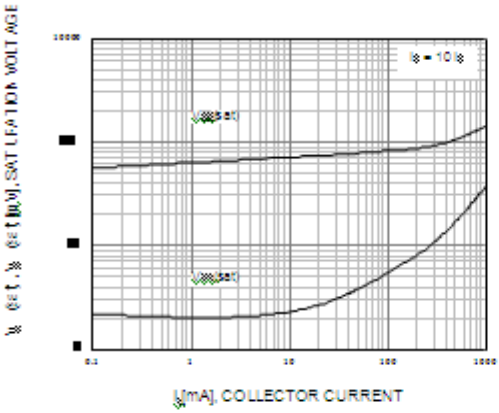
ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

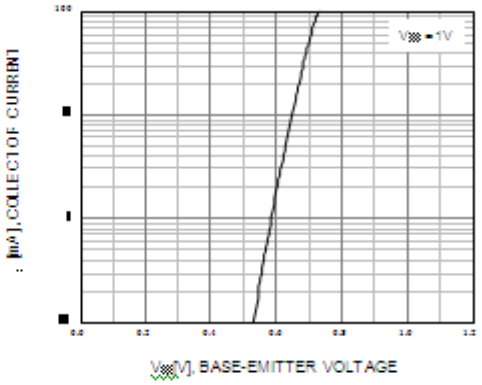
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 100μA, I_E=0	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= 0.1mA, I_B=0	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=40V, I_E=0			0.1	μA
Collector cut-off current	I_{CEO}	V_{CB}=20V, I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 5V, I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=1V, I_C= 100mA	200		350	
	$h_{FE(2)}$	V_{CE}=1V, I_C= 800mA	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=800mA, I_B= 80mA			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=800mA, I_B= 80mA			1.2	V
Transition frequency	f_T	V_{CE}=10V, I_C= 50mA f=30MHz	100			MHz

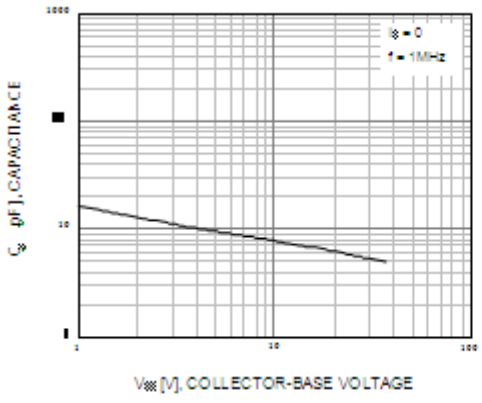
Typical Characteristics

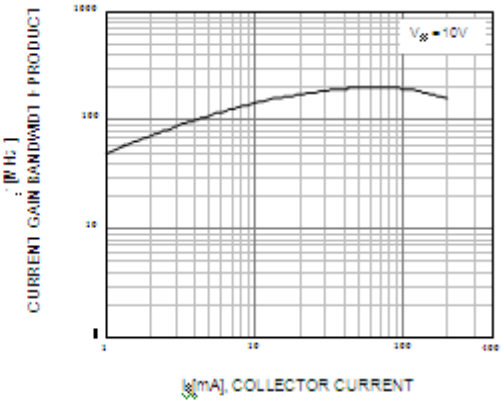






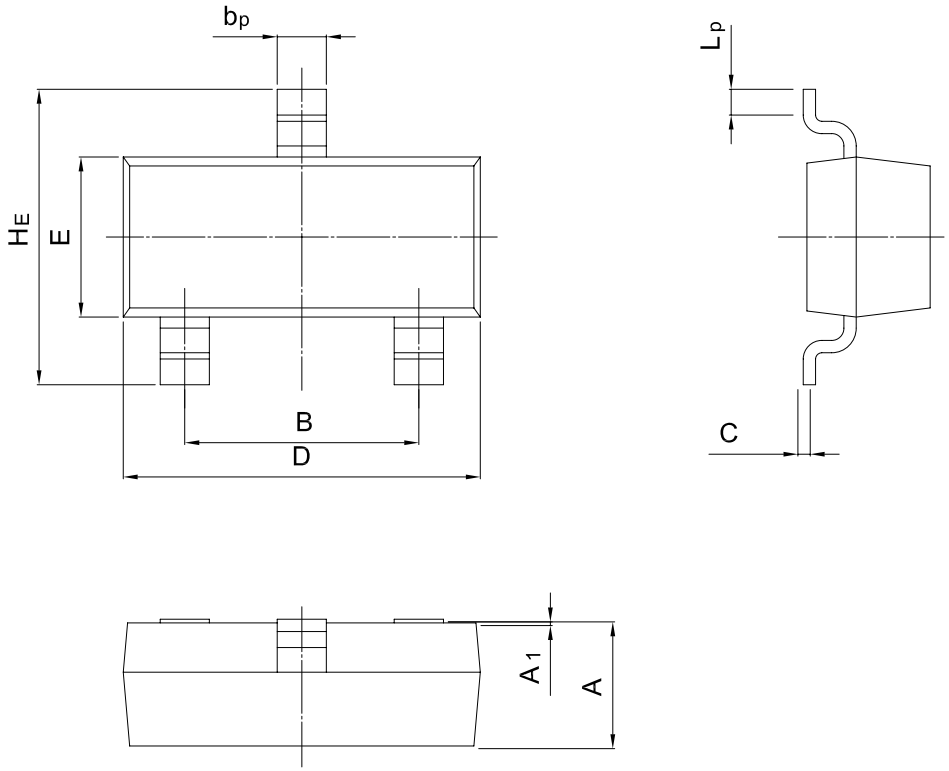






PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT-23**



UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20